

Notice of References CitedApplication No.
09/362,504Applicant(s)
Kramadhati et alExaminer
Rudy ZervigonGroup Art Unit
1763

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	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
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B	5,795,452	8/1998	Kinoshita et al	204	298.37
C	4,887,005	12/1989	Rough et al	315	111.21
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H					
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	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
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NON-PATENT DOCUMENTS

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V	H. Ramarotafika et al, "Influence of a d.c. substrate bias on the resistivity, composition, crystallite size and microstrain of WTi and WTi-N films", Thin Solid Films, 267-273	1/1995
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